

HSS100

FEATURES :

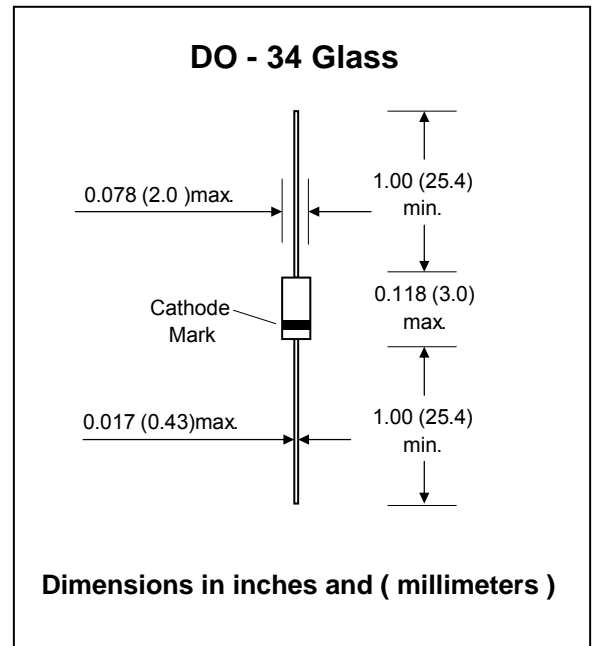
- Very Low I_R
- Low V_F and high efficiency.
- Pb / RoHS Free

MECHANICAL DATA :

Case: DO-34 Glass Case

Weight: approx. 0.11g

SCHOTTKY BARRIER DIODE



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified)

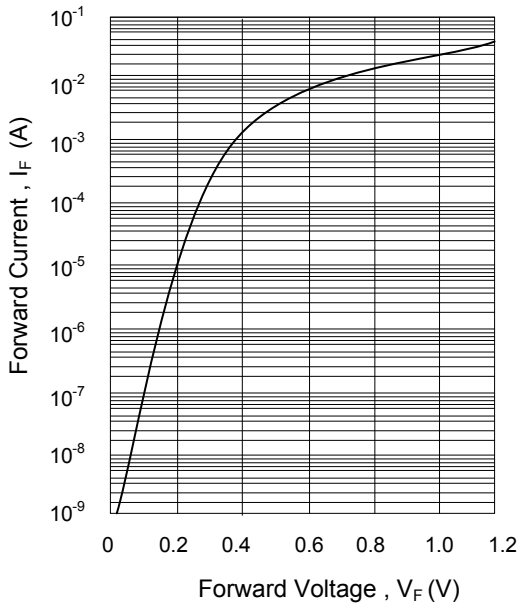
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	60	V
Average Rectified Current	I_o	35	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	125	°C
Storage temperature range	T_{stg}	-65 to + 125	°C

Electrical Characteristics (Ta = 25°C unless otherwise noted)

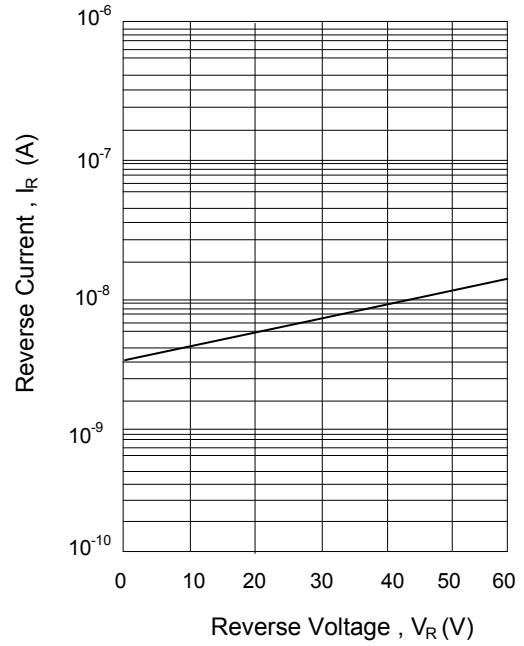
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	I_R	$V_R = 50$ V	-	-	100	nA
Reverse Voltage	V_R	$I_R = 10$ μ A	60	-	-	V
Forward Voltage	V_F	$I_F = 10$ mA	-	-	0.42	V
		$I_F = 20$ mA	-	-	0.90	V
Diode Capacitance	Cd	$V_R = 0$ V, f = 1MHz	-	-	2.2	pF
Diode Capacitance Deviation	Δ Cd	$V_R = 0$ V, f = 1MHz	-	-	0.2	pF
Forward Voltage Deviation	Δ V_F	$I_F = 20$ mA	-	-	10	mV

RATING AND CHARACTERISTIC CURVES (HSS100)

Forward Current VS. Forward Voltage



Reverse Current VS. Reverse Voltage



Diode capacitance VS. Reverse Voltage

